

# N-Channel MOSFET

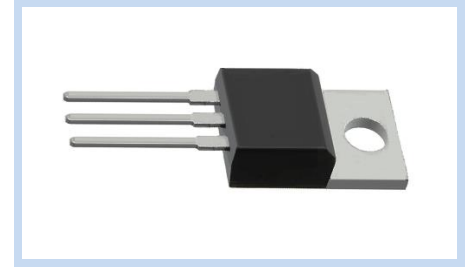
## 650V 46.7A 305W TO-220

MFT65N46T220

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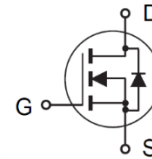
### FEATURE

- $R_{DS(ON)} < 56m\Omega$  at  $V_{GS}=10V$ ,  $I_D=20A$
- High Power and Current Handling Capability
- Super High Dense Cell Design for Extremely Low  $R_{DS(ON)}$



### MECHANICAL DATA

- Case: TO-220 Package
- Terminals: Solderable per MIL-STD-750, Method 2026

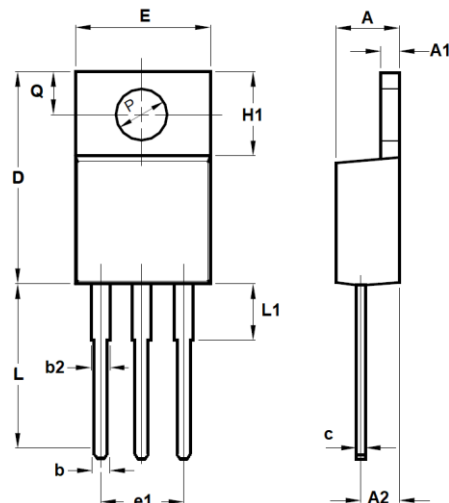


### MAXIMUM RATINGS

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DS}$	650	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V	
Drain Current – Continuous	$I_D$	$T_C=25^\circ C$	46.7	A
		$T_C=100^\circ C$	29.5	A
Drain Current – Pulsed	$I_{DM}$	187	A	
Power Dissipation	$P_D$	$T_C=25^\circ C$	305	W
		Derate above $25^\circ C$	2.44	W/ $^\circ C$
Single Pulsed Avalanche Energy	$E_{AS}$	469	mJ	
Single Pulsed Avalanche Current	$I_{AS}$	5	A	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	62.5	$^\circ C/W$	
Thermal Resistance Junction to Case	$R_{\theta JC}$	0.41	$^\circ C/W$	
Operating Junction and Storage Temperature	$T_J, T_{STG}$	-55 to 150	$^\circ C$	

### DIMENSIONS

Item	Min (mm)	Max (mm)
A	4.320	4.826
A1	1.220	1.397
A2	2.032	2.921
b	0.610	0.910
b2	1.143	1.778
c	0.356	0.530
D	14.224	16.510
E	9.652	10.668
e1	5.080	5.080
H1	5.842	6.858
L	12.700	14.732
L1	3.400	4.000
Q	2.540	3.429



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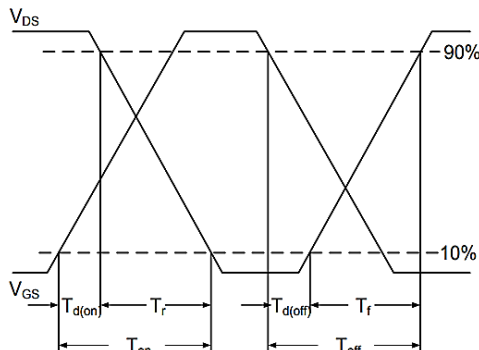
### ELECTRICAL CHARACTERISTICS

Off Characteristics	Conditions	Symbol	Min	Typ.	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	$BV_{DSS}$	650	-	-	V
Drain-Source Leakage Current	$V_{DS}=650V, V_{GS}=0V$	$I_{BSS}$	-	-	1	$\mu A$
Gate-Body Leakage Current, Forward	$V_{GS}=20V, V_{DS}=0V$	$I_{GSSF}$	-	-	100	nA
Gate-Body Leakage Current, Reverse	$V_{GS}=-20V, V_{DS}=0V$	$I_{GSSR}$	-	-	-100	nA
On Characteristics	Conditions	Symbol	Min	Typ.	Max	Unit
Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=20A$	$R_{DS(ON)}$	-	46	56	m $\Omega$
Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	$V_{GS(th)}$	2.5	-	4.5	V
Dynamic Characteristics	Conditions	Symbol	Min	Typ.	Max	Unit
Total Gate Charge	$V_{DS}=520V, V_{GS}=10V, I_D=10A$	$Q_g$	-	100	-	nC
Gate-Source Charge		$Q_{gs}$	-	17	-	
Gate-Drain Charge		$Q_{gd}$	-	41	-	
Turn-On Delay Time	$V_{DD}=520V, V_{GS}=10V, R_G=10\Omega, I_D=10A$	$T_{d(on)}$	-	45	-	ns
Rise Time		$T_r$	-	23	-	
Turn-Off Delay Time		$T_{d(off)}$	-	199	-	
Fall Time		$T_f$	-	10	-	
Input Capacitance	$V_{DS}=100V, V_{GS}=0V, F=1MHz$	$C_{iss}$	-	2935	-	pF
Output Capacitance		$C_{oss}$	-	125	-	
Reverse Transfer Capacitance		$C_{rss}$	-	10	-	
Drain-Source Body Diode	Conditions	Symbol	Min	Typ.	Max	Unit
Drain-Source Diode Forward Current	-	$I_S$	-	-	46.7	A
Diode Forward Voltage	$V_{GS}=0V, I_S=10A, T_J=25^\circ C$	$V_{SD}$	-	-	1.5	V
Reverse Recovery Time	$I_D = 20A, di/dt = 75A/\mu s$	$T_{rr}$	-	449	-	ns
Reverse Recovery Charge		$Q_{rr}$	-	5.71	-	$\mu C$
Peak Reverse Recovery Current		$I_{rr}$	-	21.7	-	A

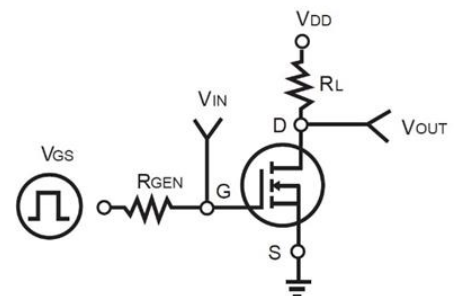
**Note:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$
3. Guaranteed by design, not subject to production testing.
4. Limited only by maximum temperature allowed.
5. Pulse Width Limited by safe operating area.
6. Full package VSD test condition  $I_S = 24.7A$ .
7.  $L=37.5mH, I_{AS} = 5A, V_{DD}= 60V, R_G=25\Omega$ , Starting  $T_J=25^\circ C$

Switching Time Waveform



Switching Test Circuit



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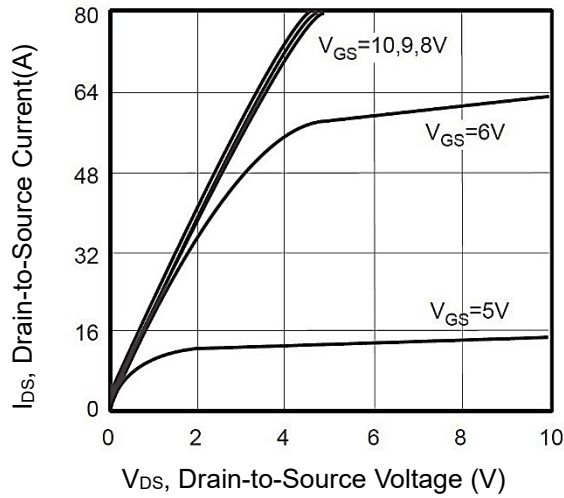
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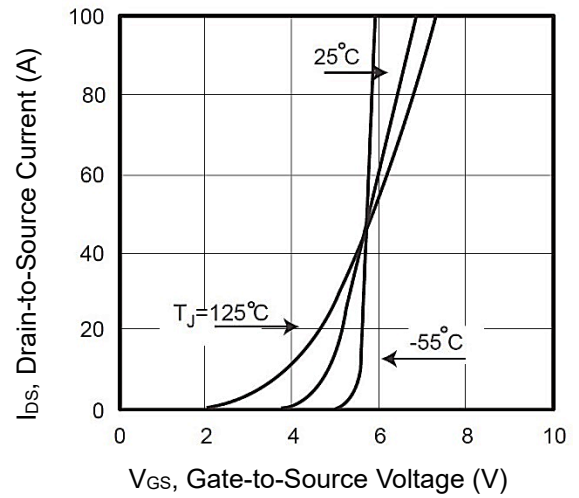
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### CHARACTERISTIC CURVES

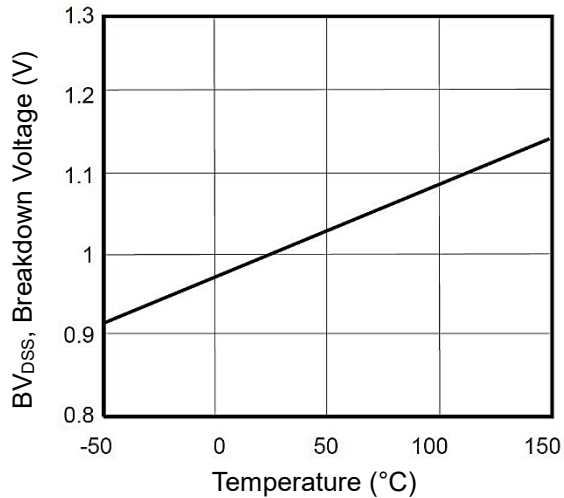
Output Characteristics



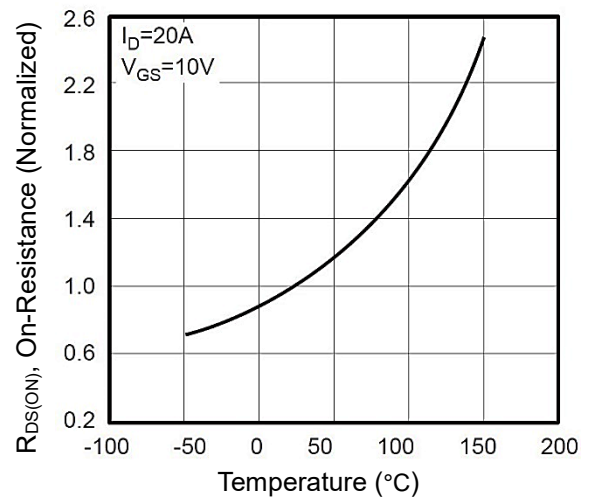
Transfer Characteristics



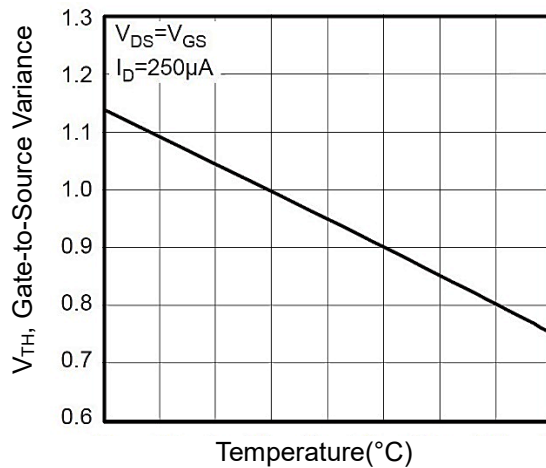
Breakdown Voltage vs. Temperature



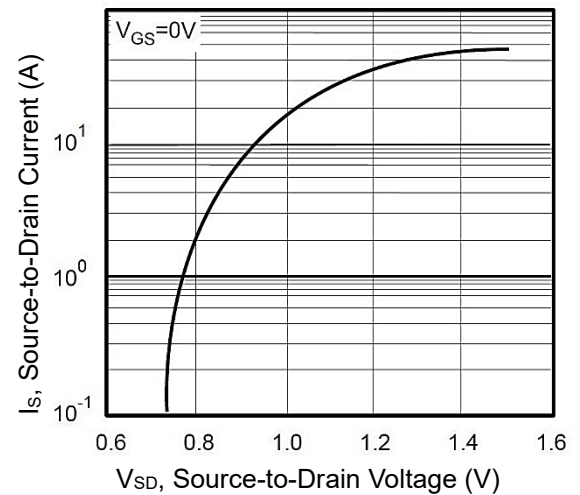
On-Resistance vs. Junction temperature



Threshold Voltage Variation with Temperature



Body Diode Characteristics



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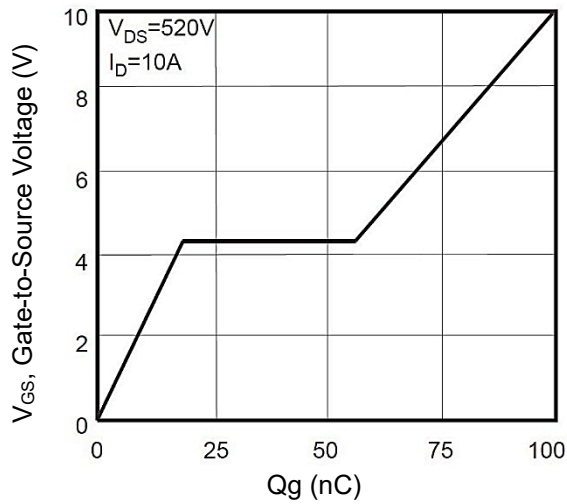
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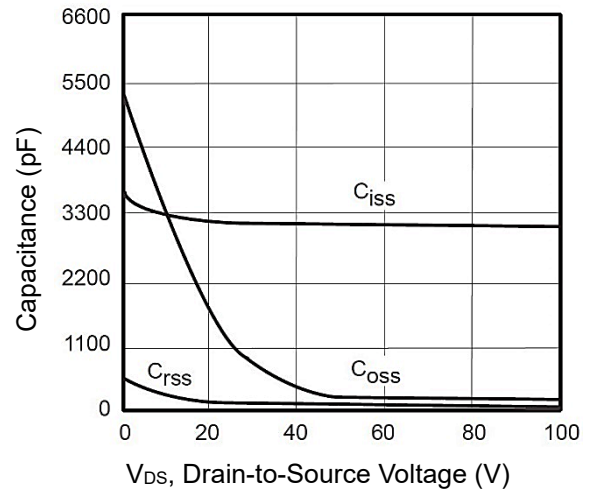
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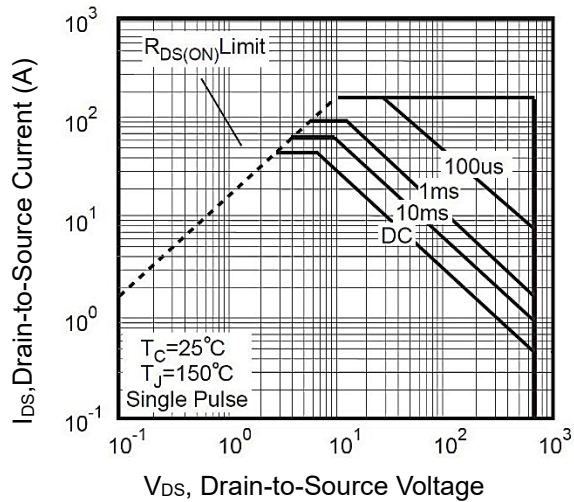
Gate-Charge Characteristics



Capacitance vs. Drain-Source Voltage



Maximum Safe Operating Area



Normalized Transient Thermal Impedance vs Pulse Width

